

## **CLAIM AMENDMENTS**

Please amend the claims as described below. In accordance with 37 CFR §1.121, a complete listing of all claims in the application is provided below. Notably, the status of each claim is indicated in the parenthetical expression adjacent to the claim number.

Claims 1 - 20 (**canceled**).

- 1        21. (NEW): A semiconductor manufacturing device comprising,  
2            a vacuum device;  
3            a mechanical drive part, wherein the mechanical drive part is capable of being  
4            moved in the vacuum device while holding a substrate;  
5            a discharge port to introduce inert gas into the vacuum device;  
6            a flow rate control part, coupled to the discharge port, to control a rate of flow of the  
7            inert gas into the vacuum device; and  
8            an inspection processing part capable of inspecting the substrate when the substrate  
9            is disposed in the vacuum device.
  
- 1        22. (NEW): The semiconductor manufacturing device of claim 21 wherein the  
2            mechanical drive part is located between the discharge port and a vacuum exhaust port in  
3            the vacuum device.
  
- 1        23. (NEW): The semiconductor manufacturing device of claim 21 wherein the  
2            mechanical drive part is adapted to translate, rotate or tilt the substrate.

1        24. (NEW): The semiconductor manufacturing device of claim 21 further including a  
2        flow rate controller to control the flow of inert gas into the vacuum device.

1        25. (NEW): The semiconductor manufacturing device of claim 24 wherein the  
2        mechanical drive part, while holding the substrate within the vacuum device, is capable of  
3        moving the substrate, relative to the inspection processing part, to permit sequential  
4        inspection of a plurality of regions of the substrate by the inspection processing part.

1        26. (NEW): A semiconductor manufacturing device comprising,  
2        a vacuum device;  
3        a mechanical drive part that is moved in the vacuum device while holding a  
4        substrate;  
5        a discharge port to introduce an inert gas into the vacuum device;  
6        a flow rate control part to control the inert gas that is discharged into the vacuum  
7        device from the discharge port at a constant flow rate; and  
8        a vacuum pump connected to the vacuum device wherein:  
9                  the total evacuation rate of the vacuum pump connected to the  
10          vacuum device is more than 300 Liters per second and less than 5,000 Liters  
11          per second;  
12          the degree of vacuum within the vacuum device is higher than  
13           $133 \times 10^{-7}$  kilo Pascals and lower than  $133 \times 10^{-4}$  kilo Pascals; and  
14          the flow rate of the inert gas is more than  $0.5 \text{ cm}^3$  per minute and less  
15          than  $20 \text{ cm}^3$  per minute.

1        27. (**NEW**): The semiconductor manufacturing device of claim 26 wherein the  
2        mechanical drive part is located between the discharge port and a vacuum exhaust port in  
3        the vacuum device.

1        28. (**NEW**): The semiconductor manufacturing device of claim 26 wherein the  
2        mechanical drive part is adapted to translate, rotate or tilt the substrate.

1        29. (**NEW**): The semiconductor manufacturing device of claim 26 further including a  
2        flow rate controller to control the flow of inert gas into the vacuum device.

1        30. (**NEW**): A semiconductor manufacturing device comprising:  
2        a vacuum chamber;  
3        a mechanical driver disposed in the vacuum chamber, wherein the mechanical driver  
4        is adapted to (i) hold a semiconductor substrate and (ii) translate, rotate or tilt the  
5        semiconductor substrate;  
6        a discharge port that introduces an inert gas into the vacuum chamber; and  
7        a flow rate controller, coupled to the discharge port, to control the flow of the inert  
8        gas through the discharge port.

1        31. (**NEW**): The semiconductor manufacturing device of claim 30 wherein the flow  
2        rate controller provides a constant rate of rate of the inert gas into the vacuum chamber.

1       32. (NEW): The semiconductor manufacturing device of claim 30 wherein the  
2 discharge port is positioned in the vicinity of the semiconductor substrate when the  
3 semiconductor substrate is located in the vacuum chamber during inspection.

1       33. (NEW): The semiconductor manufacturing device of claim 30 further including  
2 an exhaust port in the vacuum chamber.

1       34. (NEW): The semiconductor manufacturing device of claim 34 wherein the  
2 mechanical driver is positioned between the discharge port and the exhaust port.

1       35. (NEW): The semiconductor manufacturing device of claim 30 further including  
2 an inspection processing part which is capable of inspecting the semiconductor substrate  
3 when the semiconductor substrate is disposed in the vacuum chamber.

1       36. (NEW): The semiconductor manufacturing device of claim 35 wherein the  
2 mechanical driver, while holding the semiconductor substrate in the vacuum chamber, is  
3 capable of moving the semiconductor substrate, relative to an inspection processing part,  
4 to permit sequential inspection of a plurality of regions of the semiconductor substrate by  
5 the inspection processing part.

1       37. (NEW): A semiconductor manufacturing device comprising:  
2           a vacuum chamber;  
3           an inspection part disposed in the vacuum chamber;

4           a mechanical driver disposed in the vacuum chamber, wherein the mechanical driver  
5   is capable of holding a semiconductor substrate in the vacuum chamber;  
6           a discharge port that introduces an inert gas into the vacuum chamber; and  
7           a flow rate controller, coupled to the discharge port, to control the flow of inert gas  
8   through the discharge port.

1           38. (NEW): The semiconductor manufacturing device of claim 37 wherein the  
2   mechanical driver is adapted to translate, rotate or tilt the semiconductor substrate.

1           39. (NEW): The semiconductor manufacturing device of claim 37 wherein the  
2   mechanical driver, while holding the semiconductor substrate in the vacuum chamber, is  
3   capable of moving the semiconductor substrate, relative to an inspection part, to permit  
4   sequential inspection of a plurality of regions of the semiconductor substrate by the  
5   inspection part.

1           40. (NEW): The semiconductor manufacturing device of claim 37 wherein the flow  
2   rate controller provides a constant rate of rate of the inert gas into the vacuum chamber.

1           41. (NEW): The semiconductor manufacturing device of claim 37 wherein the  
2   discharge port is positioned in the vicinity of the semiconductor substrate when the  
3   semiconductor substrate is located in the vacuum chamber during inspection.

1        42. (NEW): The semiconductor manufacturing device of claim 37 further including  
2        an exhaust port in the vacuum chamber.

1        43. (NEW): The semiconductor manufacturing device of claim 42 wherein the  
2        mechanical driver is positioned between the discharge port and the exhaust port.

1        44. (NEW): The semiconductor manufacturing device of claim 42 further including a  
2        vacuum pump connect to the exhaust port.

1        45. (NEW): The semiconductor manufacturing device of claim 44 wherein the  
2        vacuum pump includes an evacuation rate of between 300 liters per second and 5,000  
3        liters per second.

1        46. (NEW): The semiconductor manufacturing device of claim 44 wherein the flow  
2        rate controller controls the flow of inert gas through the discharge port to be above 0.5 cm<sup>3</sup>  
3        per minute.

1        47. (NEW): The semiconductor manufacturing device of claim 44 wherein the flow  
2        rate controller controls the flow of inert gas through the discharge port to be below about 20  
3        cm<sup>3</sup> per minute.

1        48. (NEW): The semiconductor manufacturing device of claim 44 wherein the  
2        vacuum is above about 133 x 10<sup>-7</sup> kiloPascals and below about 133 x 10<sup>-4</sup> kiloPascals.